Amendments to the Specification:

Please amend the specification as follows:

1) Please replace the Abstract with the following:

[~~Problemsp~~ Problems] To provide a semiconductor device including a MIS-type FET having an excellent characteristic of low leakage current despite use of a high-K material of a high dielectric constant in a gate insulating film. [Means for solving Problems] A MIS-type field-effect-transistor (FET) including: a silicon substrate (1); an insulating film (6) formed on the silicon substrate and containing silicon and at least one of nitrogen and oxygen; a metal oxide film formed on the insulating film and containing silicon and hafnium; and a gate electrode formed on the metal oxide film, wherein a silicon molar ratio (Si/(Si+Hf)) in the meal oxide film is in the range of 2 to 15%.

2) Please replace the paragraph starting at page 13, line 11, with the following rewritten paragraph:

The second point of the principle is that silicon scarcely enters crystallized HfO2, if the silicon concentration is lower. FIG. 7 shows the relationship between the silicon concentration measured by TEM EELS in the crystals and the silicon concentration of the film as a whole. This figure reveals that the silicon scarcely exists in the crystals until the silicon concentration (Si/(Si+Hf)) of the film as a whole reaches 15% and is expelled to the grain boundaries (crystal grain boundaries), and that a large amount of silicon is introduced into the crystals after the silicon concentration exceeds the 15%. After the silicon is introduced into the crystals, the crystallinity of [[FfO_2]] HfO_2 is damaged, whereby the dielectric constant, which have been maintained by the HfO_2 crystals having a higher crystallinity, is reduced to approach the dielectric constant of amorphous HfO_2.